GAE GREAT AMERICAN ELECTROINCS

2N5583

Silicon Epitaxial-Planar Bipolar MW NPN transistor

Package Type: TO-39

ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25°C)

SYMBOL	Rating	VALUE	UNIT
V_{CER}	Collector-Emitter Voltage R_{EB}=10Ω	30	Vdc
V_{CBO}	Collector-Base Voltage	30	Vdc
V_{EBO}	Emitter-Base Voltage	5	Vdc
I_C	Collector Current-Continuous Ta=-60...+70°C Ta=+125°C	 0.5 0.3	Adc
I_{CM}	Pulse Collector Current Q < 10 and t < 10MC	 1.0	A
P_{tot}	Total Device Dissipation Ta=-60...+25°C Ta=+125°C	 4 0.8	W
Tj	Junction Temperature	180	°C
Tstg	Storage Temperature Range	-60...+125	°C

Electrical Characteristics (T_{CASE}=25°C)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CBO}	Collector Cutoff Current V_{CB}=30Vdc		 0.3	mA
I_{EBO}	Emitter Cutoff Current V_{EB}=3Vdc		 0.1	mA
hFE	DC Current Gain V_{CB}=5Vdc, I_E=100mA	 20		
V_{CE}	Collector-Emitter Saturation Voltage I_C=100mA, I_B=10mA		 0.6	V
hfe	Current Gain Bandwidth Product V_{CE}=10V, I_E=100mA, f=300MHz	 5		
V_{BE}	Base-Emitter Saturation Voltage I_C=150mAdc, I_B=15mAdc		 1.1	Vdc